

Notice of References Cited	Application/Control No. 10/047,323	Applicant(s)/Patent Under Reexamination LAMPERT ET AL.	
	Examiner Matthew J Song	Art Unit 1765	Page 1 of 1

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	B	US-3,675,619	07-1972	Burd, John W.	118/719
	C	US-5,861,346	01-1999	Hamza et al.	438/769
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	N	JP 62091492 A	04-1987	Japan	TASHIRO, YOSHIHARU	C30B 23/08
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	U	Kaneda et al. "MBE Growth of 3C SiC/ 6H SiC and the Electric Properties of Its p-n Junction", Journal of Crystal Growth 81(1987) pg 536-542.
	V	Patent Abstracts of Japan. English Abstract of JP 62-091492 (1987).
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.